

## General Description

The HSM4606 is the high performance complementary N-ch and P-ch MOSFETs with high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The HSM4606 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

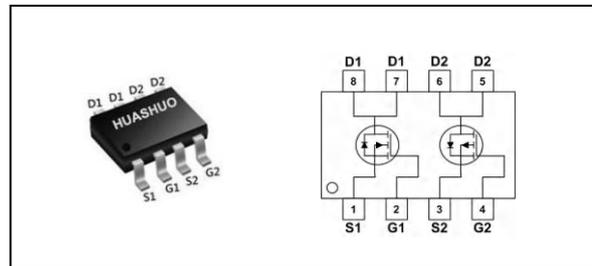
## Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

## Product Summary

BVDSS	RDSON	ID
30V	22mΩ	7A
-30V	26mΩ	-6A

## Dual SOP8 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
$V_{DS}$	Drain-Source Voltage	30	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7	-6	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.8	-4.5	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	24	-24	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	8.1	45	mJ
$I_{AS}$	Avalanche Current	12.7	-30	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	1.5	1.5	W
$T_{STG}$	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	60	$^\circ C/W$



**N-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.023	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	---	22	28	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	---	35	41	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.7	3	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.2	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =6A	---	12.8	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2.3	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	---	7	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.6	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	1.6	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =12V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =6A	---	7.7	---	ns
T <sub>r</sub>	Rise Time		---	46	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	11	---	
T <sub>f</sub>	Fall Time		---	3.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	388	---	pF
C <sub>oss</sub>	Output Capacitance		---	62	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	58	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	6	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	24	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=12.7A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



**P-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.021	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6A	---	26	32	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	---	35	56	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.7	-3.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.2	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-6A	---	12.6	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	15	---	Ω
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A	---	18.6	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	3.5	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.3	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-24V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-1A	---	16.4	---	ns
T <sub>r</sub>	Rise Time		---	20.2	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	55	---	
T <sub>f</sub>	Fall Time		---	10	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	926	---	pF
C <sub>oss</sub>	Output Capacitance		---	119	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	97	---	

**Diode Characteristics**

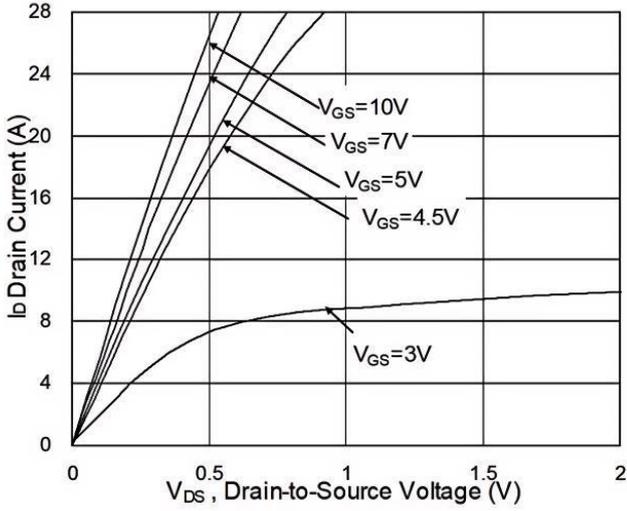
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-5.7	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	-24	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V

Note :

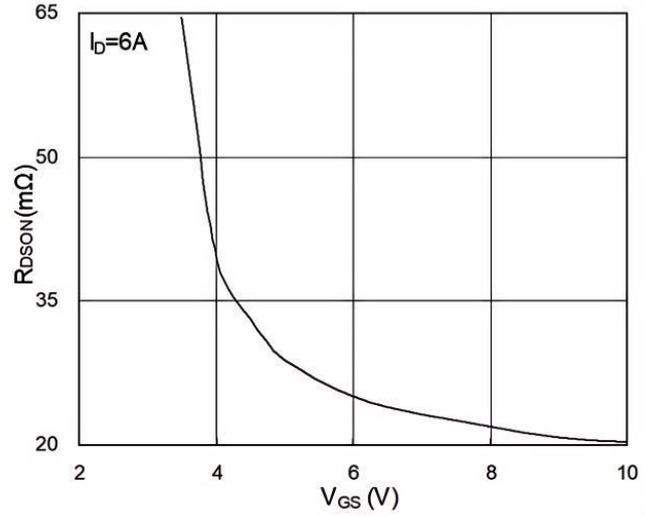
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup>FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=-25V, V<sub>GS</sub>=-10V, L=0.1mH, I<sub>AS</sub>=-30A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



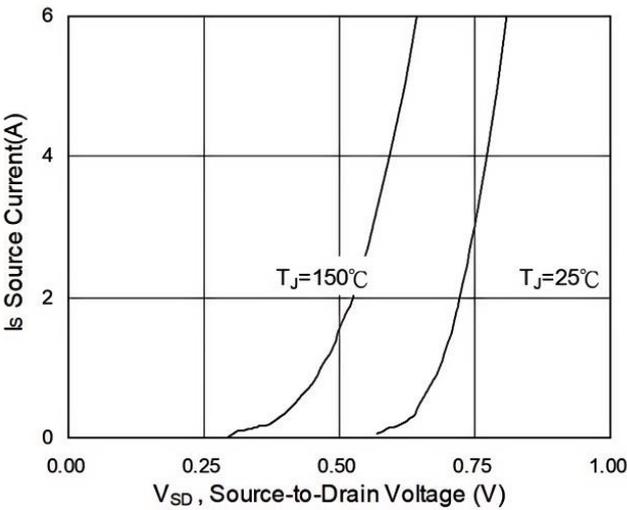
**N-Channel Typical Characteristics**



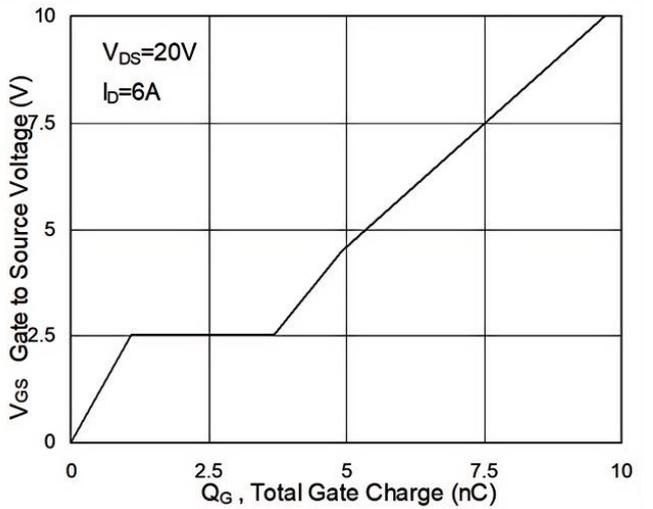
**Fig.1 Typical Output Characteristics**



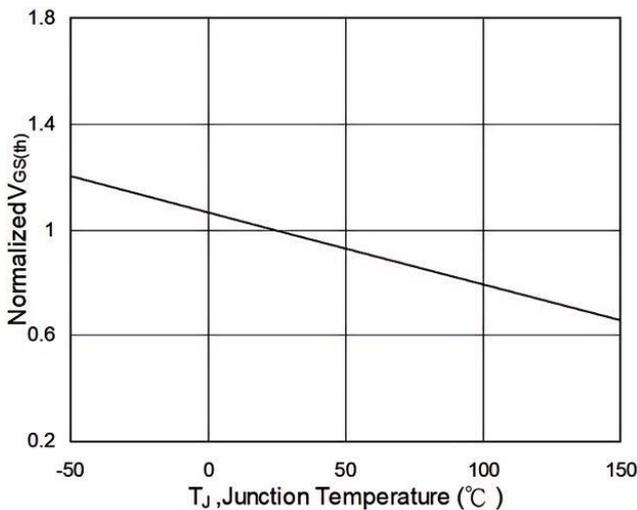
**Fig.2 On-Resistance vs. Gate-Source**



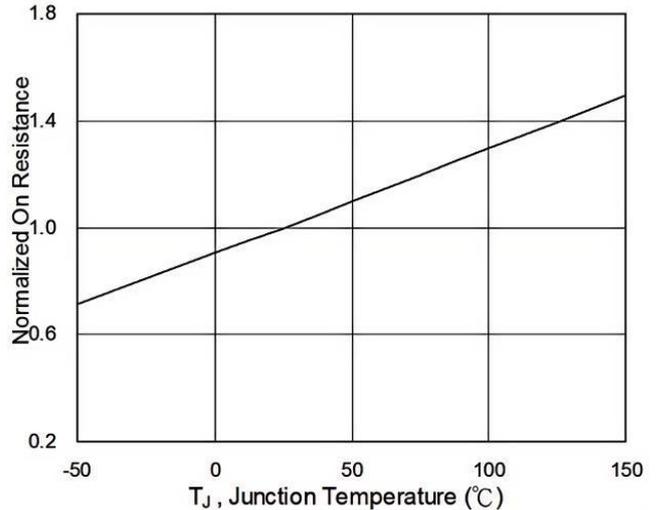
**Fig.3 Forward Characteristics Of Reverse**



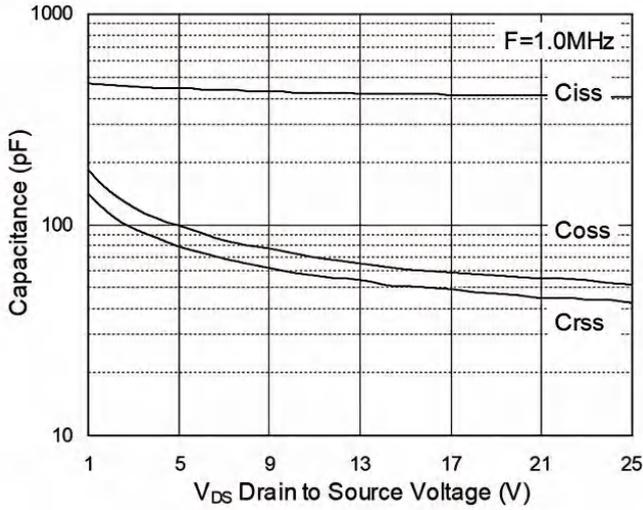
**Fig.4 Gate-Charge Characteristics**



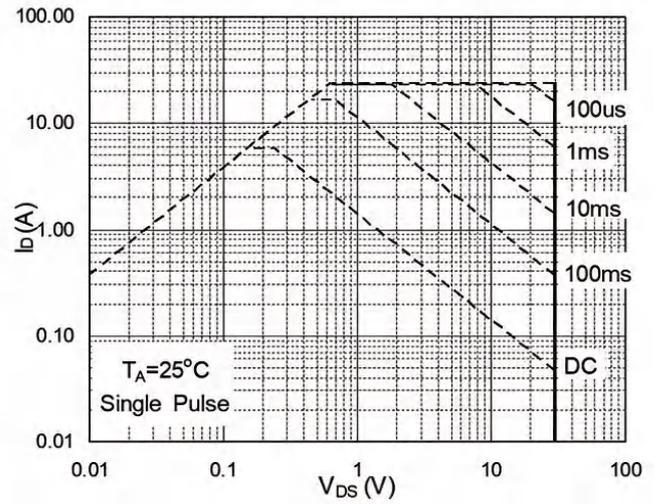
**Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>**



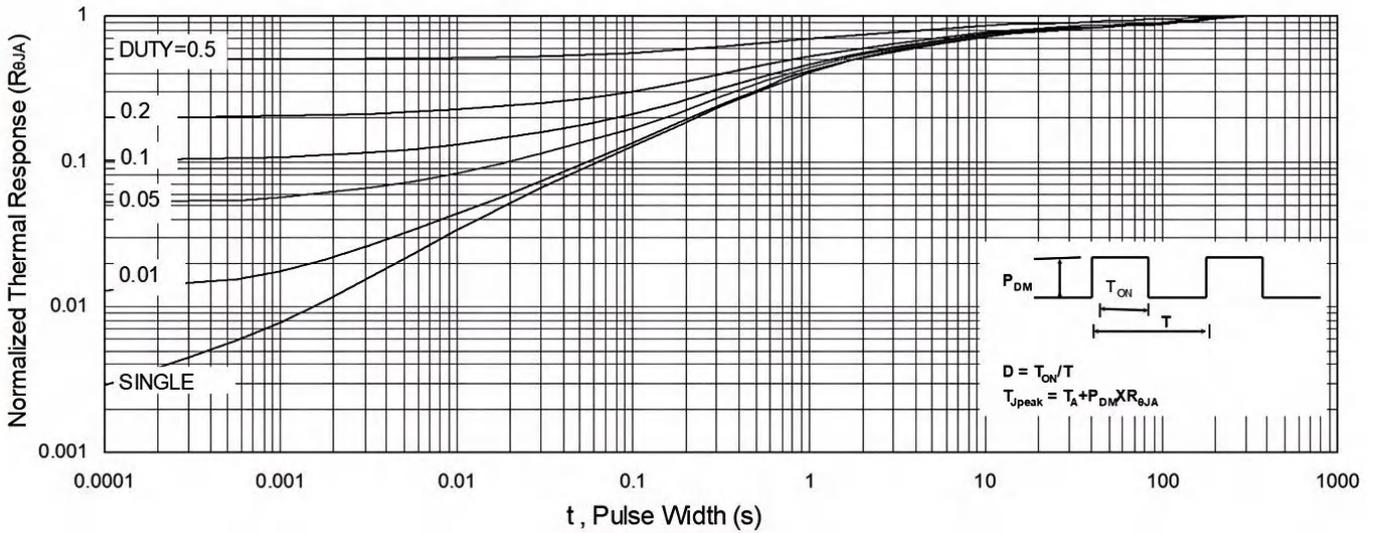
**Fig.6 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>**



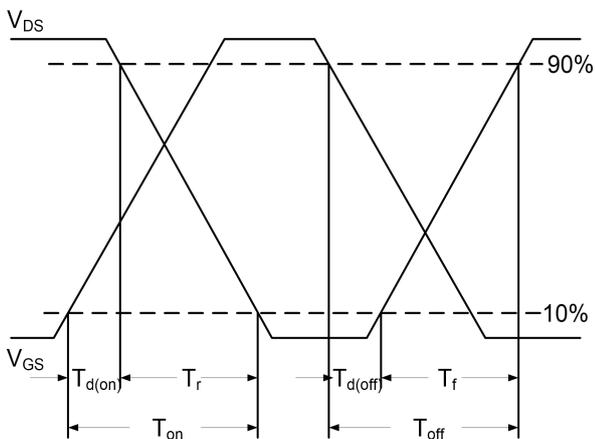
**Fig.7 Capacitance**



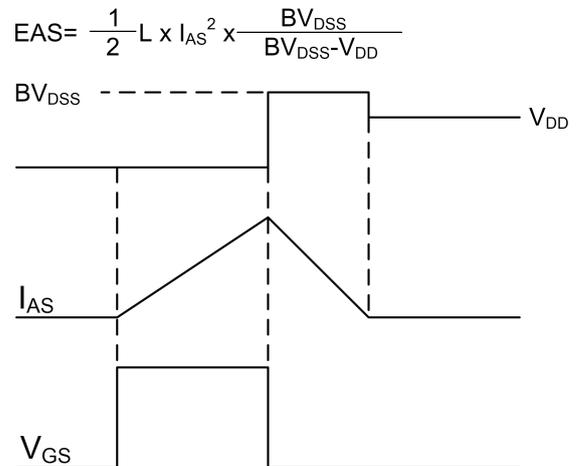
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**



P-Channel Typical Characteristics

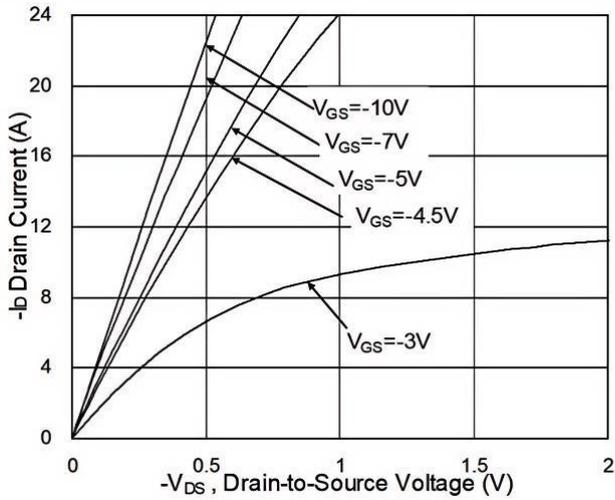


Fig.1 Typical Output Characteristics

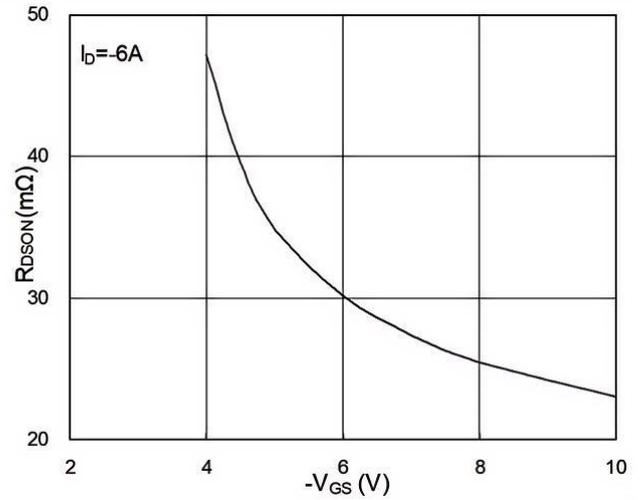


Fig.2 On-Resistance v.s Gate-Source

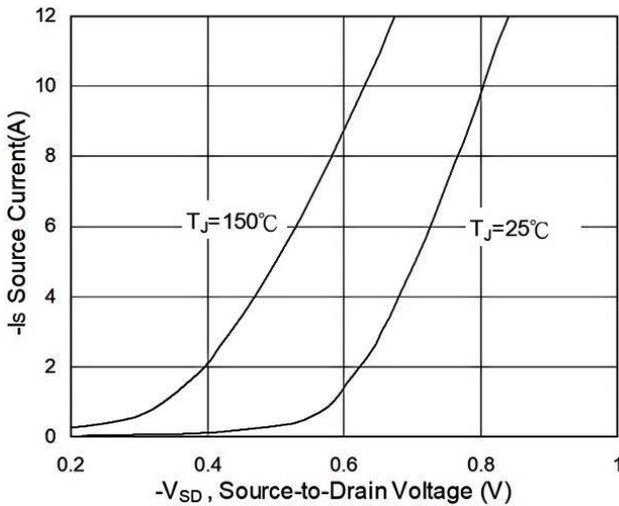


Fig.3 Forward Characteristics Of Reverse

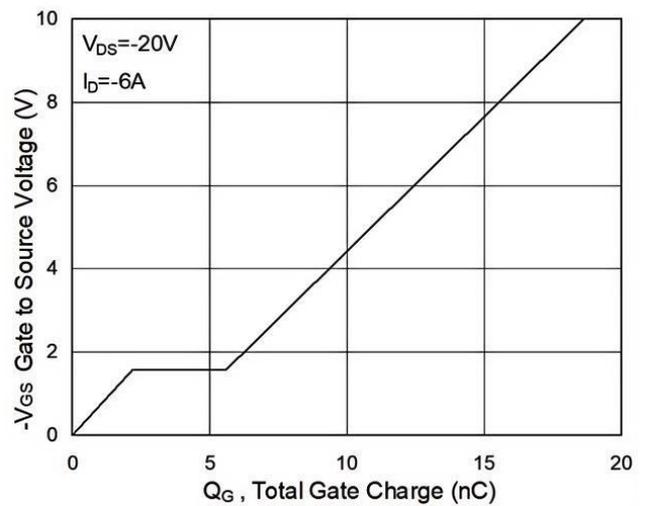


Fig.4 Gate-Charge Characteristics

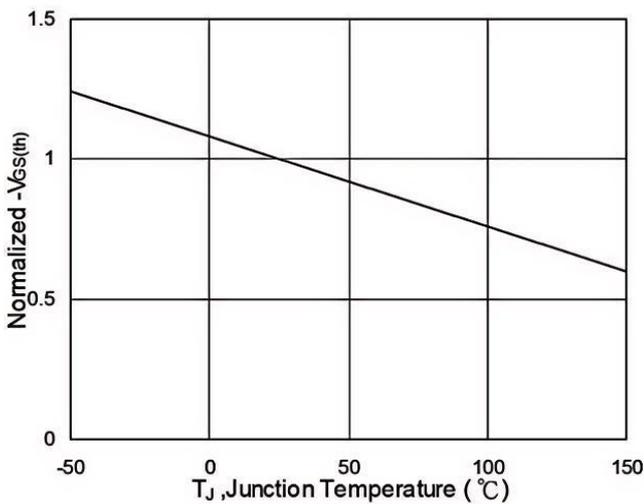


Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$

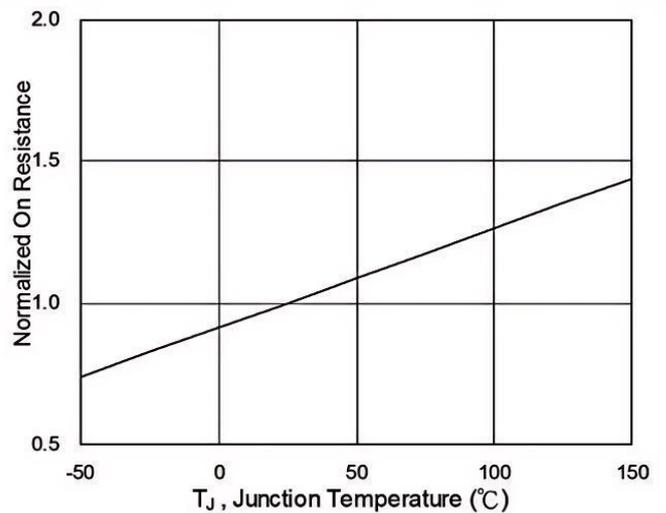
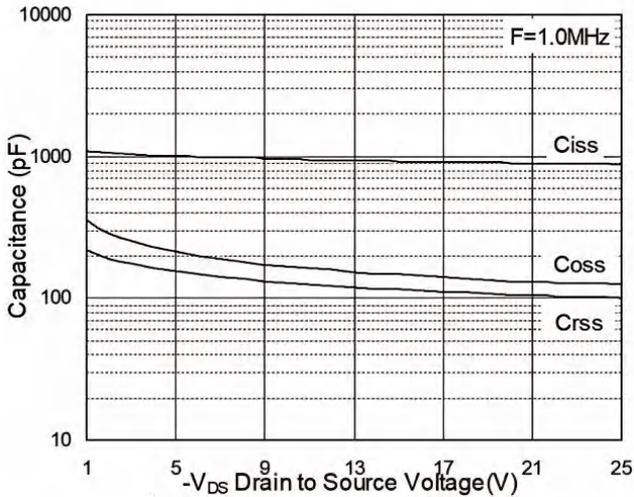
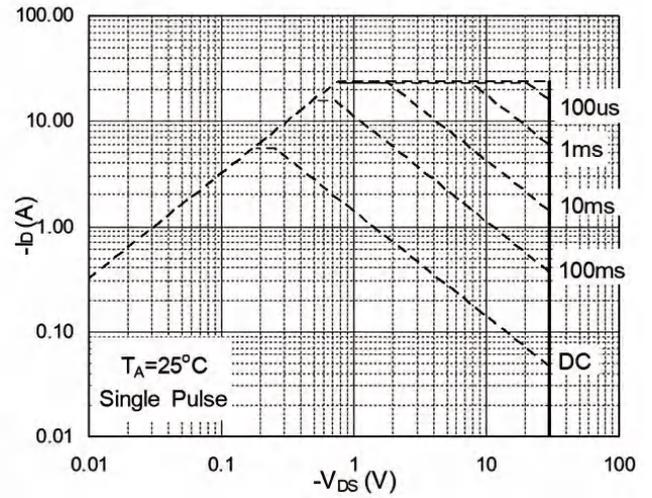


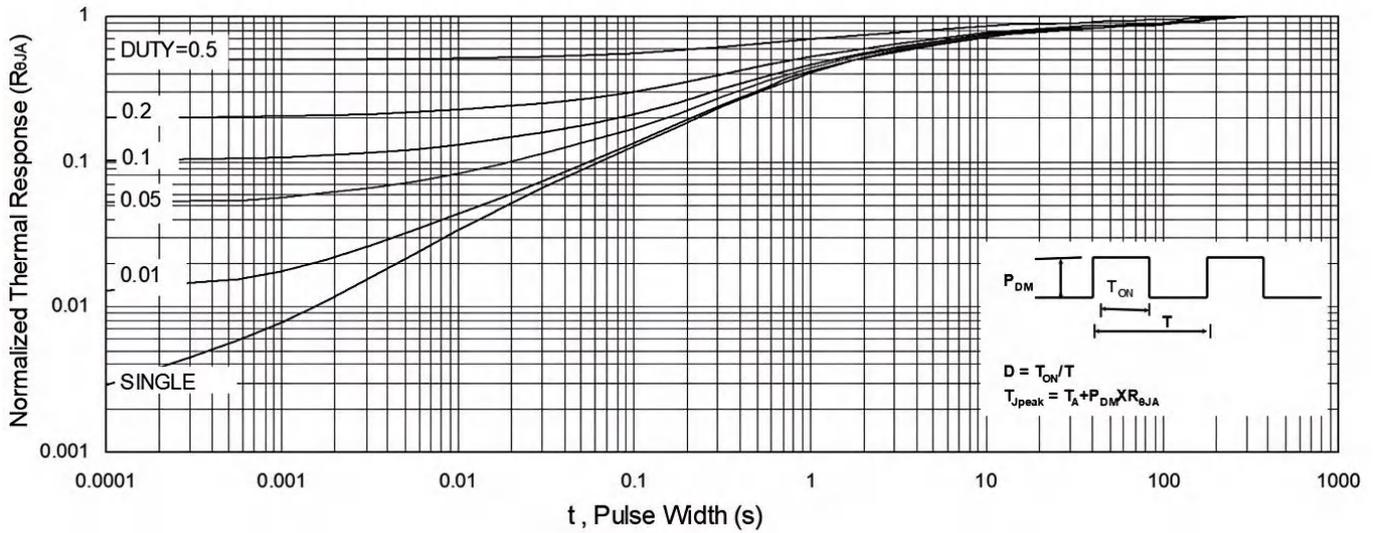
Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$



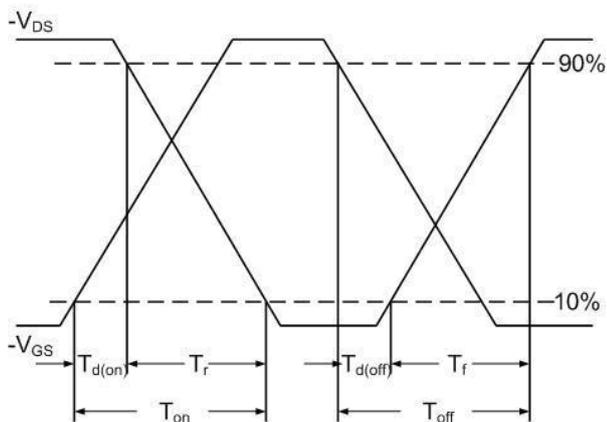
**Fig.7 Capacitance**



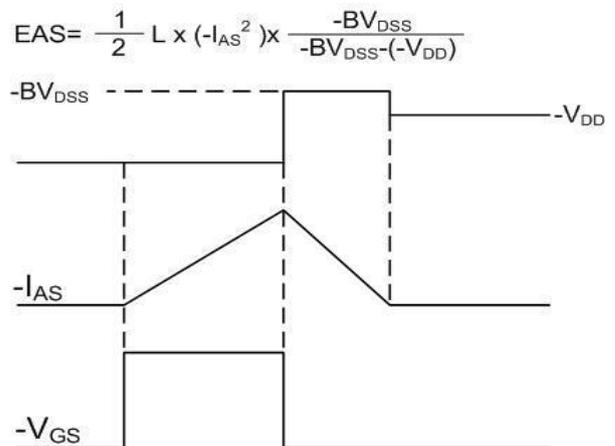
**Fig.8 Safe Operating Area**



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**Fig.10 Switching Time Waveform**



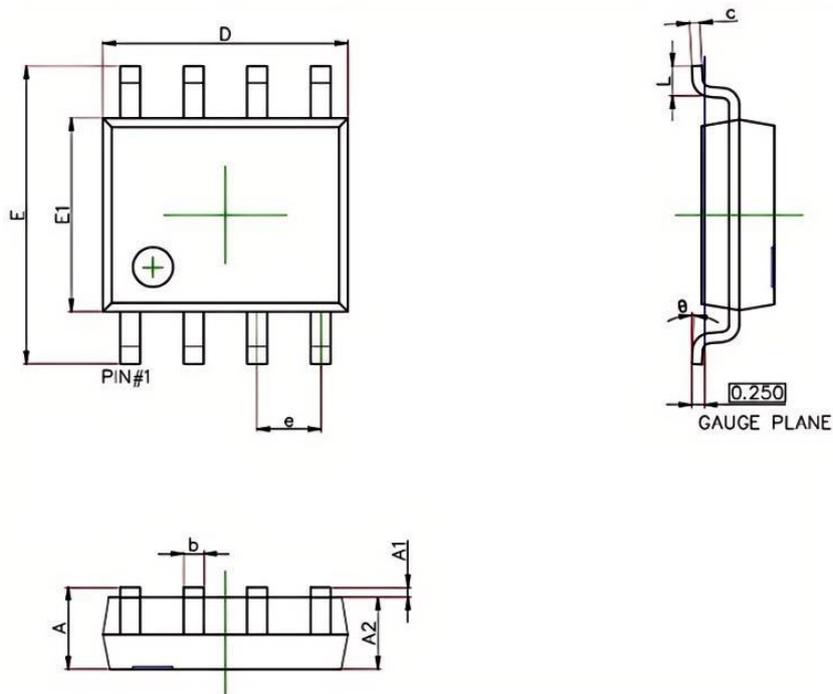
**Fig.11 Unclamped Inductive Switching Waveform**



## Ordering Information

<b>Part Number</b>	<b>Package code</b>	<b>Packaging</b>
<b>HSM4606</b>	<b>SOP-8</b>	<b>4000/Tape&amp;Reel</b>

## SOP-8 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
C	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



## HSM4606 Marking:

